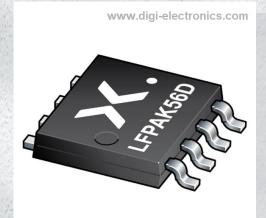


# **BUK7K17-60EX Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number BUK7K17-60EX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number BUK7K17-60EX

Description MOSFET 2N-CH 60V 30A LFPAK56D

Detailed Description Mosfet Array 60V 30A 53W Surface Mount LFPAK56

D



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RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
BUK7K17-60EX	Nexperia USA Inc.
Series:	Product Status:
-	Active
Technology:	Configuration:
MOSFET (Metal Oxide)	2 N-Channel (Dual)
FET Feature:	Drain to Source Voltage (Vdss):
	60V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ Id, Vgs:
30A	14mOhm @ 10A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 1mA	23.6nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
1578pF @ 25V	53W
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
SOT-1205, 8-LFPAK56	LFPAK56D
Base Product Number:	
RI IV7V17	

# **Environmental & Export classification**

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



# **BUK7K17-60E**

# Dual N-channel 60 V, 14 m $\Omega$ standard level MOSFET

10 December 2013

**Product data sheet** 

# 1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> of greater than 1 V at 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	-	30	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	53	W
Static characte	Static characteristics FET1 and FET2						,
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11		-	11.3	14	mΩ
Dynamic chara	Dynamic characteristics FET1 and FET2					,	
$Q_{GD}$	gate-drain charge	$I_D = 10 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	8.1	-	nC

[1] Continuous current is limited by package



Dual N-channel 60 V, 14 mΩ standard level MOSFET

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 <b>LFPAK56D (SOT1205)</b>	
8	D1	drain1	ETTAROS (3311200)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7K17-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K17-60E	71760E

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	60	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	30	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>		-	29	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	164	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	53	W

BUK7K17-60E

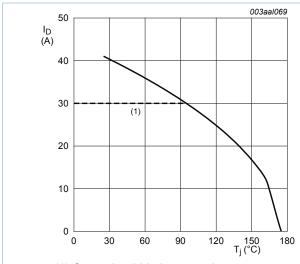
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# **BUK7K17-60E**

#### Dual N-channel 60 V, 14 m $\Omega$ standard level MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain o	Source-drain diode FET1 and FET2					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	30	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	164	Α
Avalanche Ruggedness FET1 and FET2					J	
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 30 A; $V_{sup} \le 60 \text{ V}$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Fig. 3	[2][3]	-	55	mJ

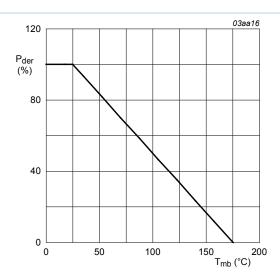
- [1] Continuous current is limited by package
- [2] Refer to application note AN10273 for further information
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



(1) Capped at 30A due to package



$$V_{GS} \ge 10V$$



ig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

#### Dual N-channel 60 V, 14 mΩ standard level MOSFET

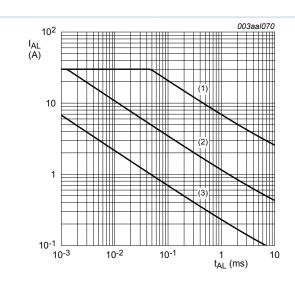
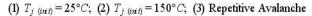


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



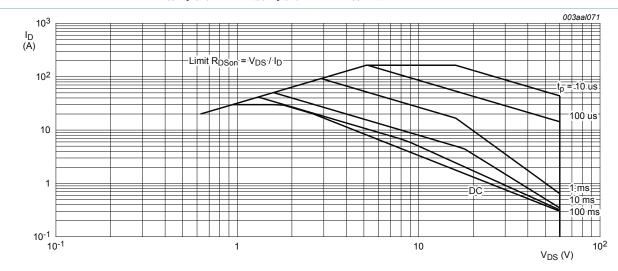


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

### 9. Thermal characteristics

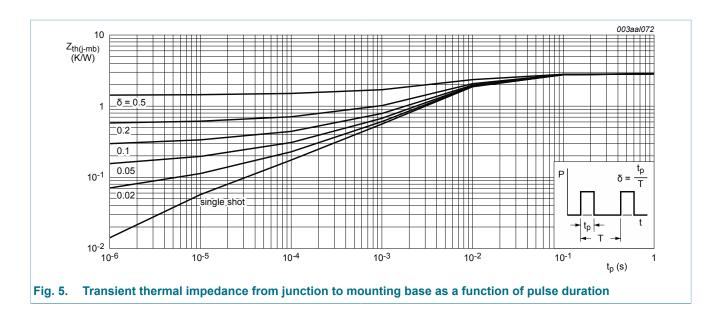
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	2.84	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

BUK7K17-60E

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#### Dual N-channel 60 V, 14 m $\Omega$ standard level MOSFET



# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2			'		_
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 9; Fig. 10	1	-	-	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; Fig. 9; Fig. 10	-	-	4.5	V	
I <sub>DSS</sub> drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA	
	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ	
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; Fig. 11	-	11.3	14	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	25.3	31.4	mΩ	
Dynamic ch	naracteristics FET1 and FE	ET2	'	1		
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 10 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V;	-	23.6	-	nC
Q <sub>GS</sub>	gate-source charge T <sub>j</sub> = 25 °C; Fig. 13; Fig. 14	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	4.9	-	nC

#### Dual N-channel 60 V, 14 m $\Omega$ standard level MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$Q_{GD}$	gate-drain charge	$I_D = 10 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$	-	8.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	1183	1578	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	167	200	pF
C <sub>rss</sub>	reverse transfer capacitance		-	113	158	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 48 \text{ V}; R_L = 5 \Omega; V_{GS} = 10 \text{ V};$	-	7.6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 10 A$	-	11.1	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	15.5	-	ns
t <sub>f</sub>	fall time		-	11	-	ns
Source-drain diode FET1 and FET2						
$V_{SD}$	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	24.5	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	24.6	-	nC

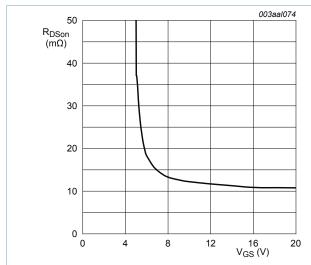


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25$ °C;  $I_D = 10A$ 

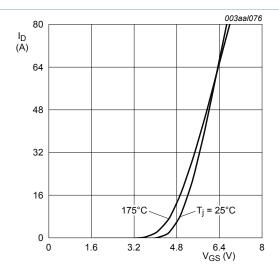


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$ 

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#### Dual N-channel 60 V, 14 mΩ standard level MOSFET

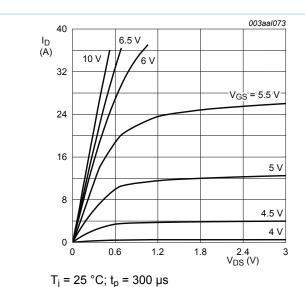


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

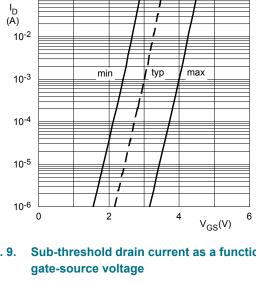


Fig. 9. Sub-threshold drain current as a function of

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

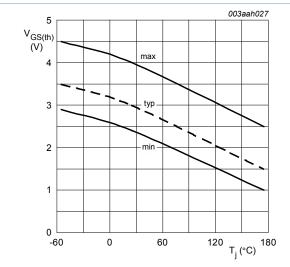
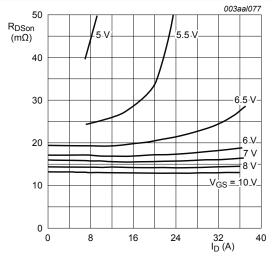


Fig. 10. Gate-source threshold voltage as a function of junction temperature

 $I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$ 



 $T_i = 25 \, ^{\circ}C; t_p = 300 \, \mu s$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

#### Dual N-channel 60 V, 14 m $\Omega$ standard level MOSFET

**BUK7K17-60E** 

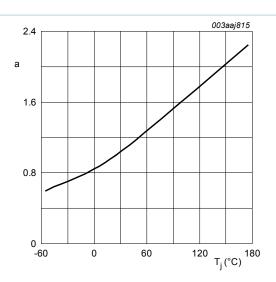


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

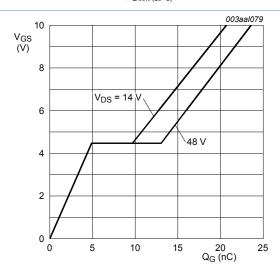


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

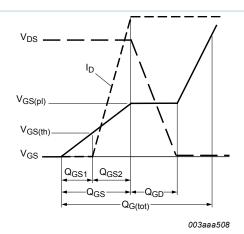


Fig. 13. Gate charge waveform definitions

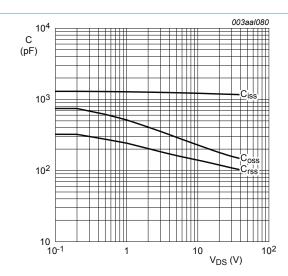


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

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#### Dual N-channel 60 V, 14 m $\Omega$ standard level MOSFET

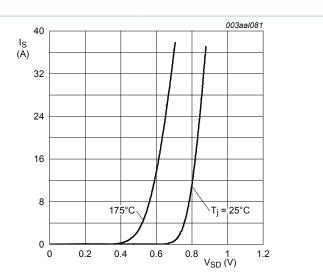
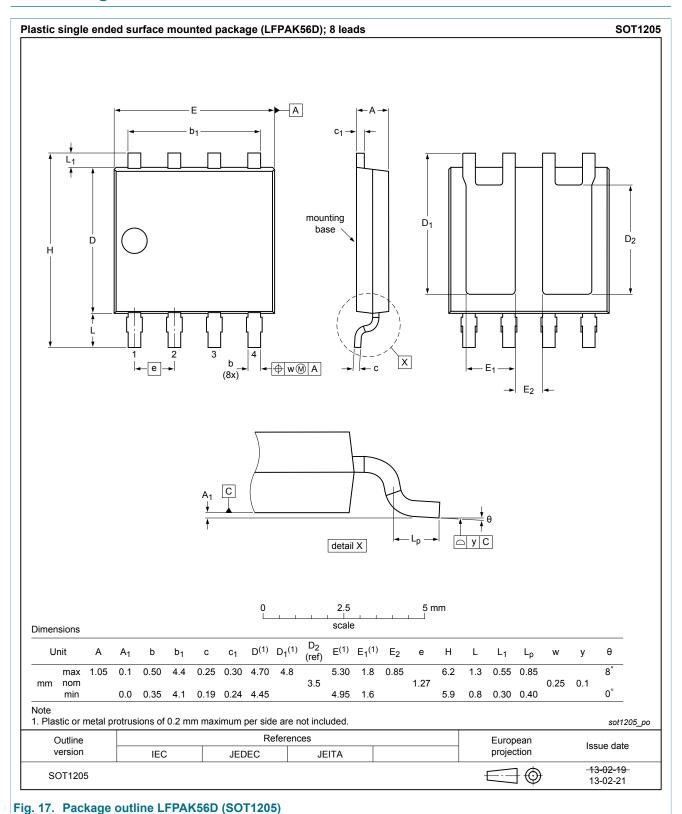


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

Dual N-channel 60 V, 14 mΩ standard level MOSFET

# 11. Package outline



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#### Dual N-channel 60 V, 14 mΩ standard level MOSFET

### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### Dual N-channel 60 V, 14 mΩ standard level MOSFET

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# **BUK7K17-60E**

#### Dual N-channel 60 V, 14 m $\Omega$ standard level MOSFET

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